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Russ Fischer a1. a1 At&T Bell Laboratories 600 Mountain Avenue Murray Hill, NJ 07974. SUMMARY ABSTRACT. Despite the 4.2% lattice mismatch, several laboratories have

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Wavelength demultiplexing stack photodiode detector with Material Aspects of GaAs and InP Based Structures, Swaminathan et al., "Material Aspects of GaAs

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Gallium arsenide - ieee conferences,

Gallium arsenide (GaAs) is a compound of the elements gallium and arsenic. (Wikipedia.org)

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